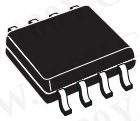
STS11NF30L

N-channel 30V - 0.0085Ω - 11A SO-8
Low gate charge STripFET™ II Power MOSFET

General features

Type	V_{DSS}	$R_{DS(on)}$	I_D
STS11NF30L	30V	<0.009Ω	11A

- Optimal R_{DS}(on) x Qg trade-off
- Conduction losses reduced

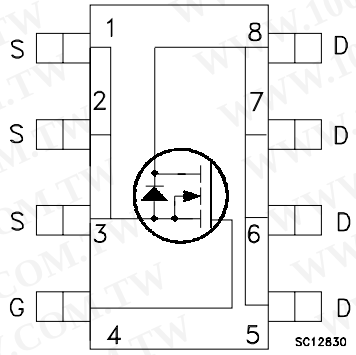


S0-8

Description

This Power MOSFET is the latest development of STMicroelectronis unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

Internal schematic diagram



Applications

- Switching application

Order codes

Part number	Marking	Package	Packaging
STS11NF30L	11F30L-	SO-8	Tape & reel

Contents

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage (V_{GS} = 0)	30	V
V_{GS}	Gate-source voltage	± 18	V
I_D(1)	Drain current (continuous) at T_C = 25°C	11	A
I_D	Drain current (continuous) at T_C = 100°C	7	A
I_{DM}(2)	Drain current (pulsed)	44	A
P_{TOT}	Total dissipation at T_C = 25°C	2.5	W
	Derating factor	0.02	W/°C
dv/dt(3)	Peak diode recovery voltage slope	5.5	V/ns
T_J T_{stg}	Operating junction temperature Storage temperature	-55 to 150 150	°C

1. Current limited by the package
2. Pulse width limited by safe operating area
3. $I_{SD} \leq 1A$, di/dt $\leq$370A/µs, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{JMAX}$

Table 2. Thermal data

R_{thj-a}	Thermal resistance junction-ambient Max(1)	50	°C/W
T_l	Maximum lead temperature for soldering purpose	150	°C

1. When Mounted on 1 inch^2 FR-4 board, 2 oz of Cu and t [10 sec

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 250 µA, V_{GS} = 0	30			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = Max rating V_{DS}=Max rating, T_C=125°C			1 10	µA µA
I_{GSS}	Gate-body leakage current (V_{DS} = 0)	V_{GS} = ± 18V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250µA	1			V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS} = 10V, I_D = 5.5A V_{GS} = 5V, I_D = 5.5A		0.0085 0.0145	0.0105 0.0190	Ω Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward transconductance	V_{DS} = 25V, I_D=5.5A		15		S
C_{iss}	Input capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		1440		pF
C_{oss}	Output capacitance			560		pF
C_{rss}	Reverse transfer capacitance			135		pF
Q_g	Total gate charge	V_{DD} = 15V, I_D = 11A, V_{GS} =5V		22.5	30	nC
Q_{gs}	Gate-source charge			9		nC
Q_{gd}	Gate-drain charge			12		nC

1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 .

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	V_{DD}=15 V, I_D=5.5A, R_G=4.7Ω, V_{GS}= 5V *(see Figure 13)*		22 39		ns ns
$t_{d(off)}$ t_f	Turn-off-delay time Fall time	V_{DD} = 15V, I_D = 5.5A, R_G = 4.7Ω, V_{GS} = 5V *(see Figure 13)*		23 16		ns ns

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current				11	A
I_{SDM} (1)	Source-drain current (pulsed)				44	A
V_{SD} (2)	Forward on voltage	I_{SD} = 11A, V_{GS} = 0			1.2	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 11A, V_{DD} = 20V di/dt = 100A/µs, T_j = 150°C *(see Figure 15)*		42 52 2.5		ns nC A

1. Pulse width limited by safe operating area.
2. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

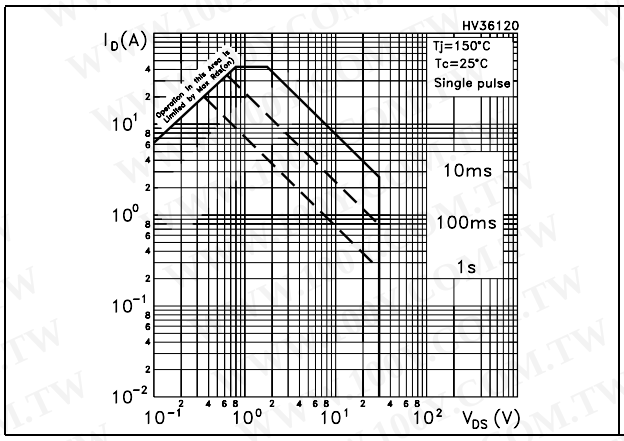


Figure 2. Thermal impedance

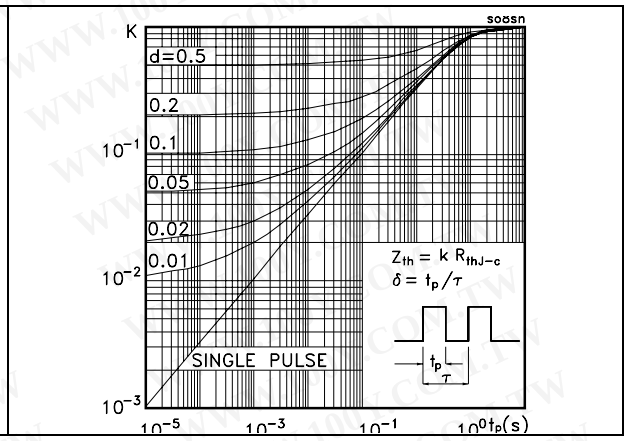


Figure 3. Output characterisics

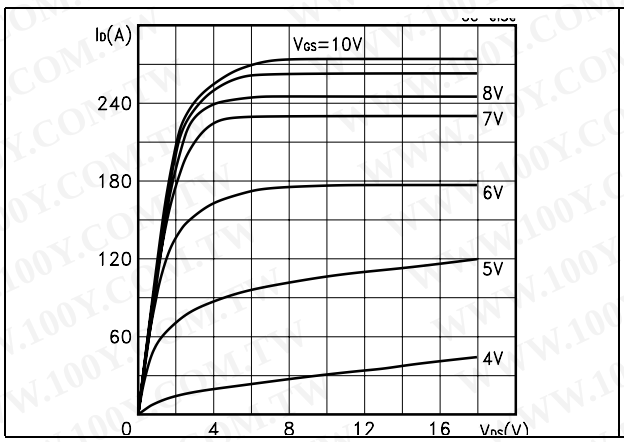


Figure 4. Transfer characteristics

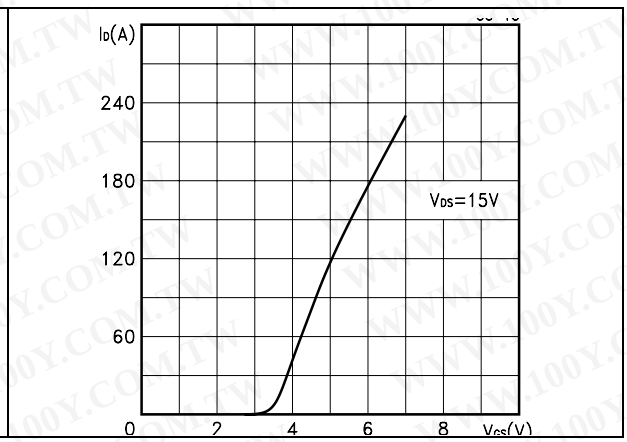


Figure 5. Transconductance

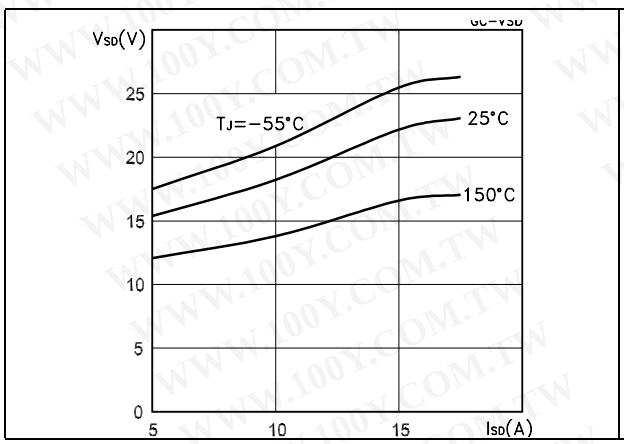


Figure 6. Static drain-source on resistance

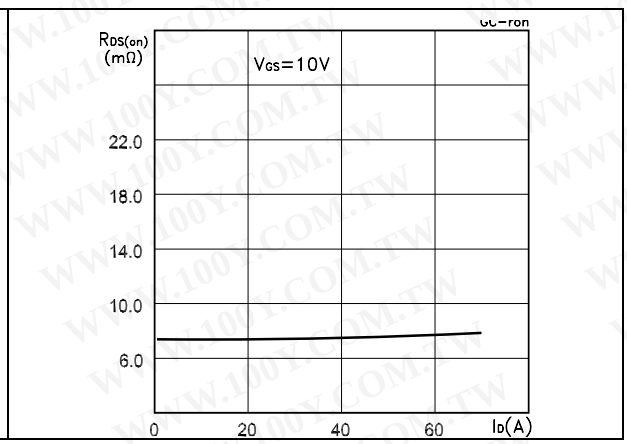


Figure 7. Gate charge vs gate-source voltage

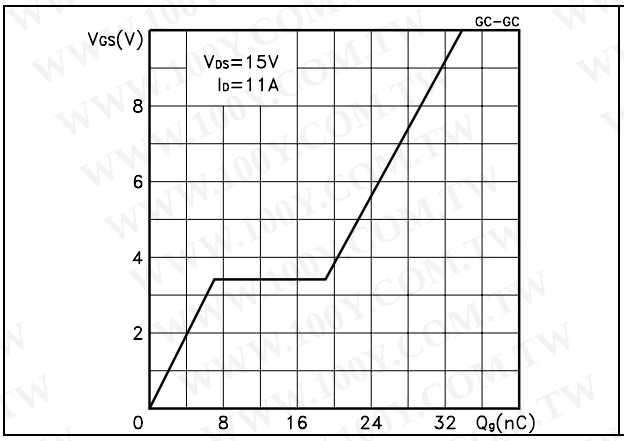


Figure 8. Capacitance variations

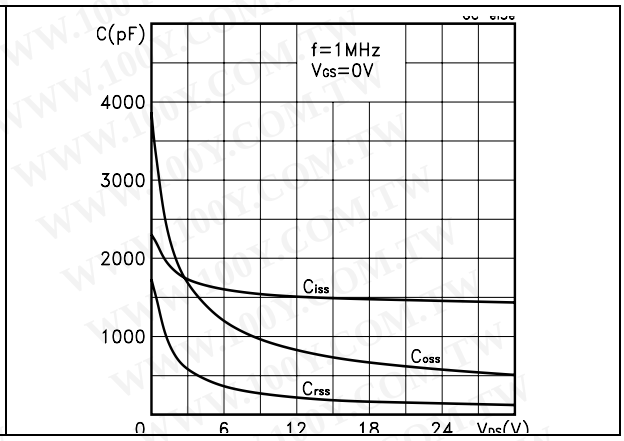


Figure 9. Normalized gate threshold voltage vs temperature

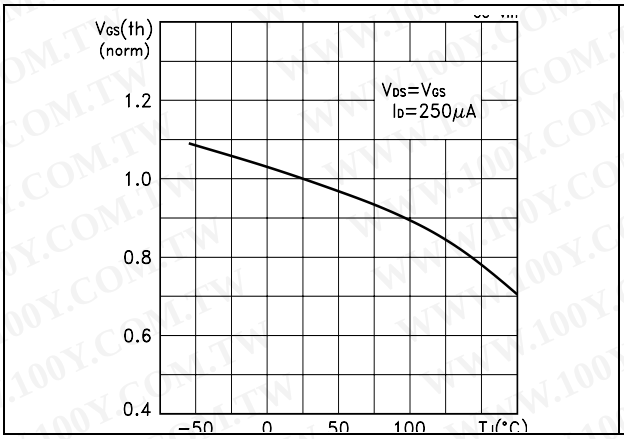


Figure 10. Normalized on resistance vs temperature

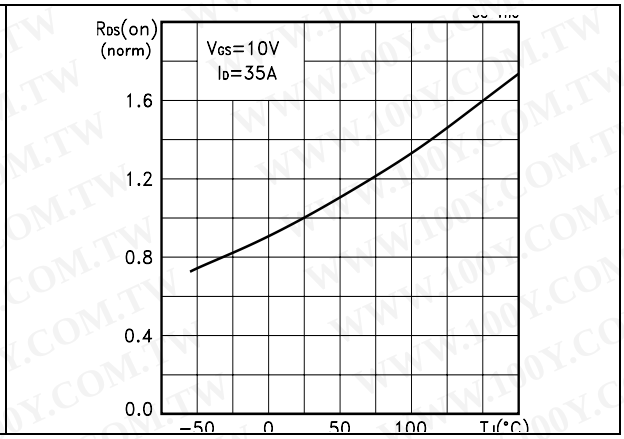


Figure 11. Source-drain diode forward characteristics

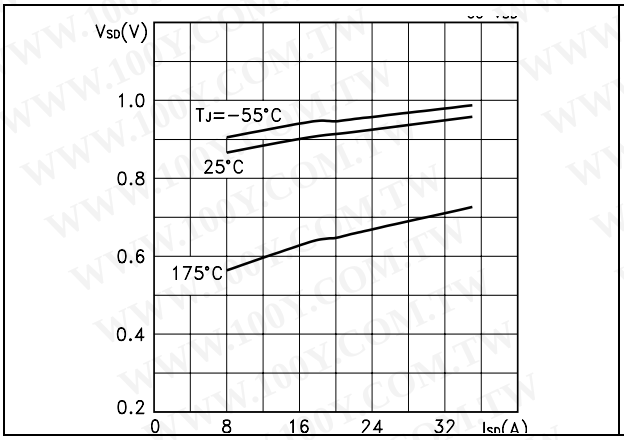
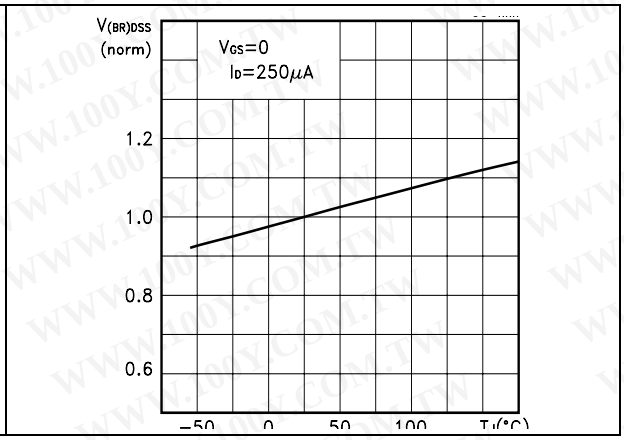


Figure 12. Normalized Breakdown Voltage vs Temperature



3 Test circuit

Figure 13. Switching times test circuit for resistive load

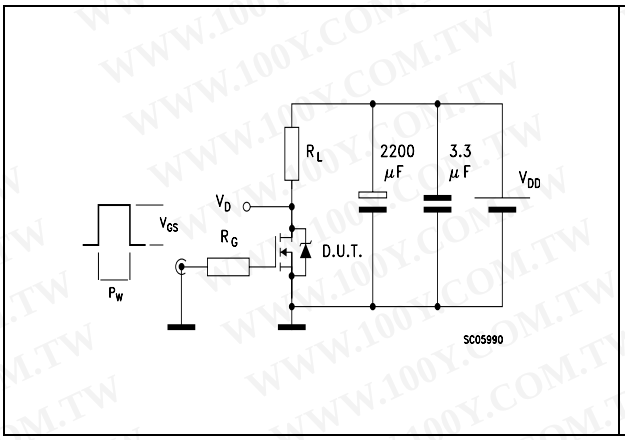


Figure 14. Gate charge test circuit

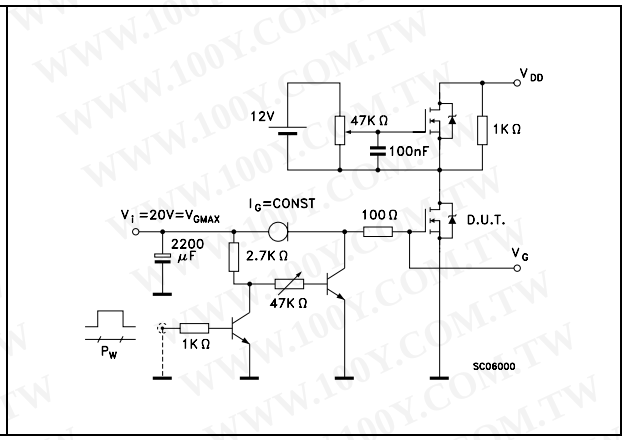


Figure 15. Test circuit for inductive load switching and diode recovery times

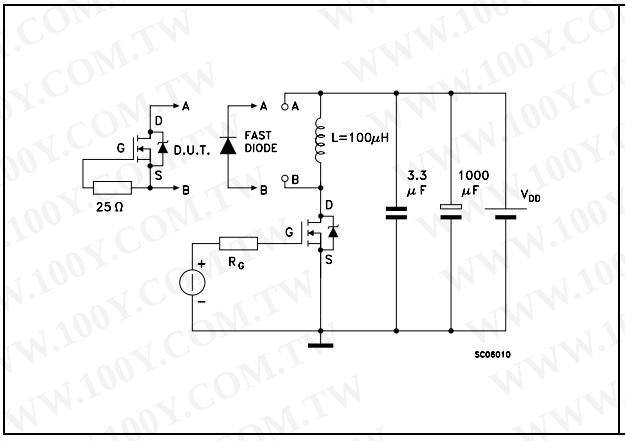


Figure 16. Unclamped Inductive load test circuit

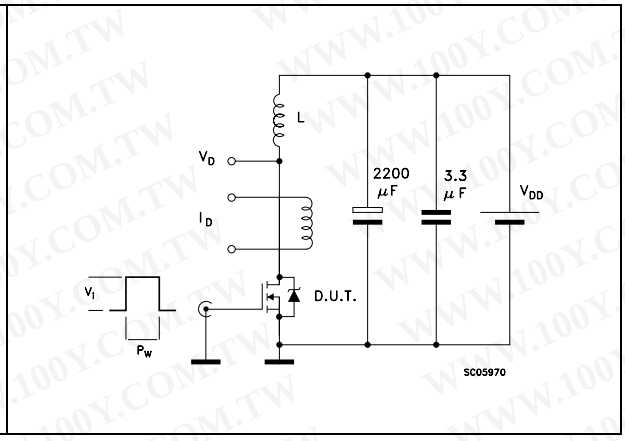


Figure 17. Unclamped inductive waveform

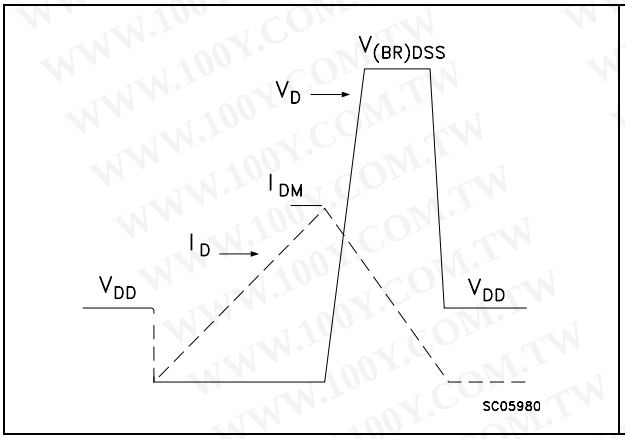
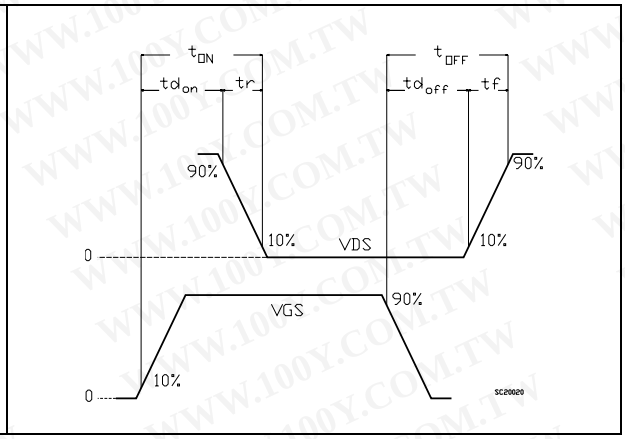


Figure 18. Switching time waveform

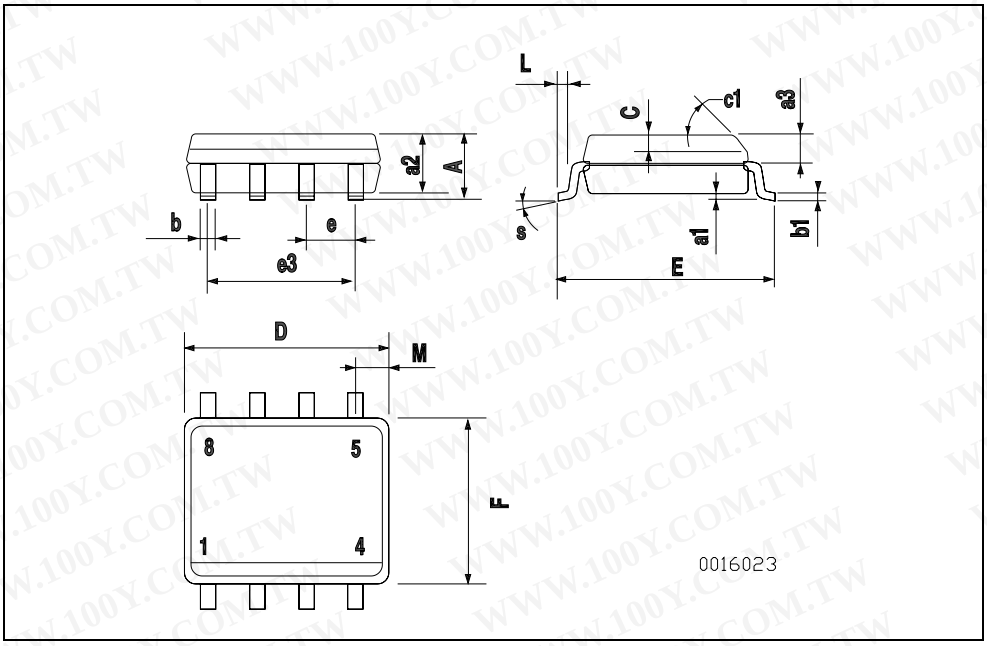


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at : *www.st.com*

SO-8 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45 (typ.)					
D	4.8		5.0	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8 (max.)					



5 Revision history

Table 7. Revision history

Date	Revision	Changes
09-Sep-2004	9	Complete version
17-Aug-2006	10	The document has been reformatted
12-Jan-2007	11	Updates in *Safe operating area*

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